Features

- Split Gate Trench MOSFET Technology
- Low Thermal Resistance
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

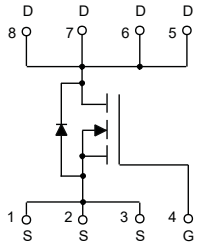
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 3.5°C/W Junction to Case (2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	80	A
	T_C=100°C		51	A
Pulsed Drain Current (3)		I_{DM}	320	A
Total Power Dissipation		P_D	35	W
Single Pulsed Avalanche Energy(4)		E_{AS}	312	mJ

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. Surface Mounted on 1 in^2 pad area, t≤10 sec.
3. Pulse Test: Pulse Width≤10μs,Duty Cycle ≤1%.
4. T_J=25°C, L=1mH, V_{DD}=50V.

Internal Structure



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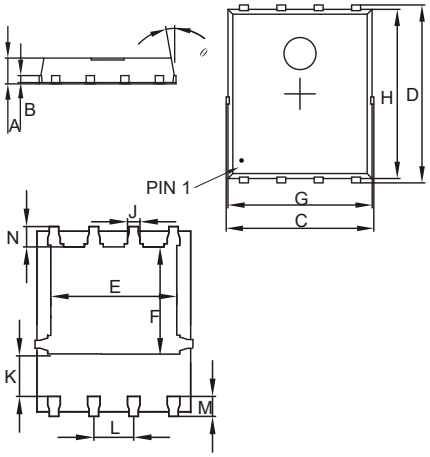


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	80			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=64V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2		4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A		2.9	3.5	mΩ
		V_{GS}=6V, I_D=10A		3.8	5	mΩ
Diode Characteristics						
Continuous Body Diode Current	I_S				80	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=20A			1.3	V
Reverse Recovery Time	t_{rr}	I_S=20A,di/dt=100A/μs		70		ns
Reverse Recovery Charge	Q_{rr}			100		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=40V,V_{GS}=0V,f=1MHz		5575		pF
Output Capacitance	C_{oss}			747		
Reverse Transfer Capacitance	C_{rss}			83		
Total Gate Charge	Q_g	V_{DS}=40V,V_{GS}=10V,I_D=20A		102		nC
Gate-Source Charge	Q_{gs}			27		
Gate-Drain Charge	Q_{gd}			26		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=40V, V_{GEN}=10V, R_G=4.5Ω, R_L=2Ω, I_{DS}=20A		20		ns
Turn-On Rise Time	t_r			35		
Turn-Off Delay Time	$t_{d(off)}$			70		
Turn-Off Fall Time	t_f			33		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

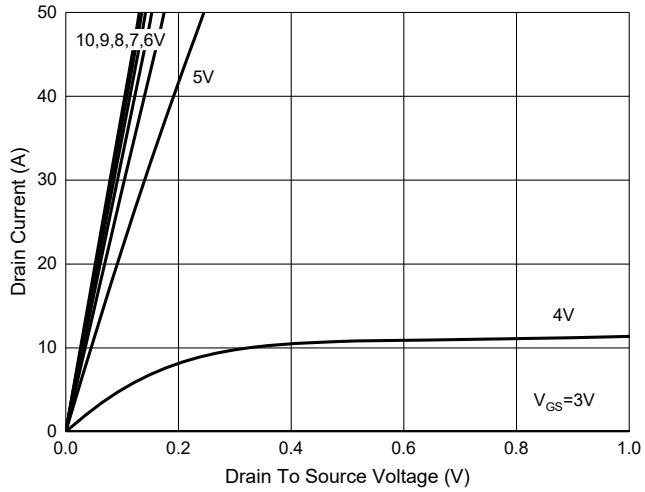


Fig. 2 - I_S—V_{SD}

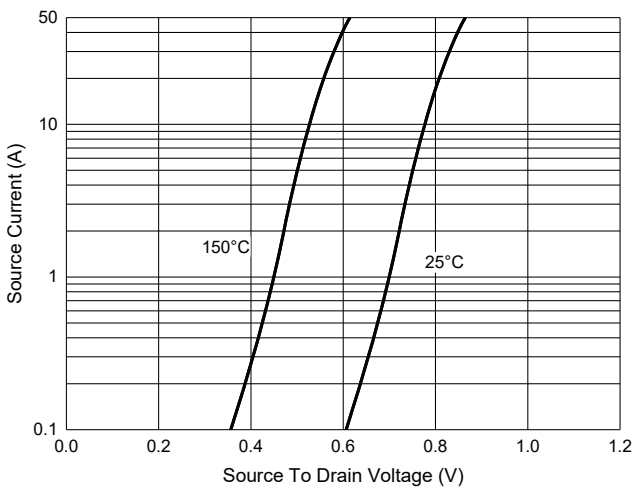


Fig. 3 - $R_{DS(ON)}$—I_D

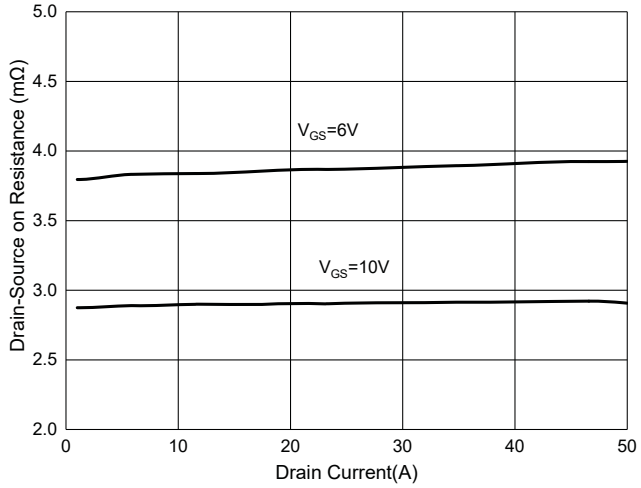


Fig. 4 - Normalized On Resistance Characteristics

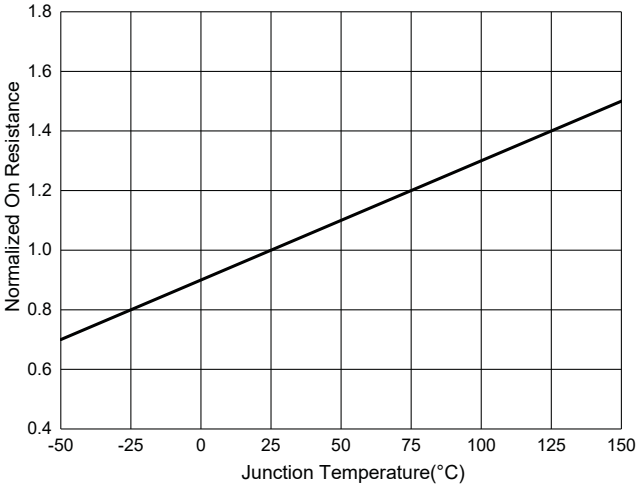


Fig. 5 - Capacitance Characteristics

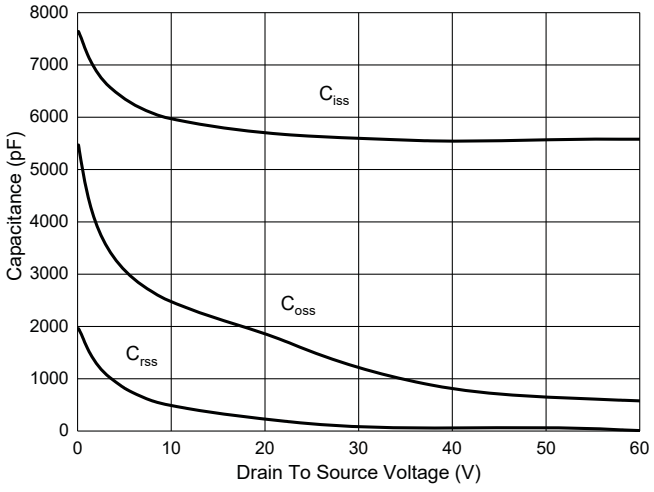
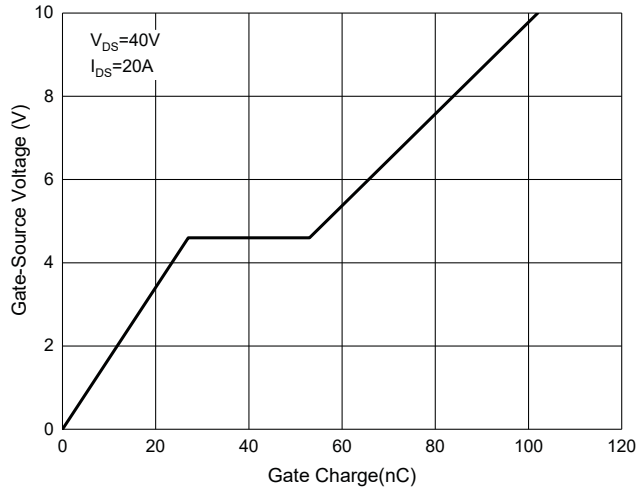
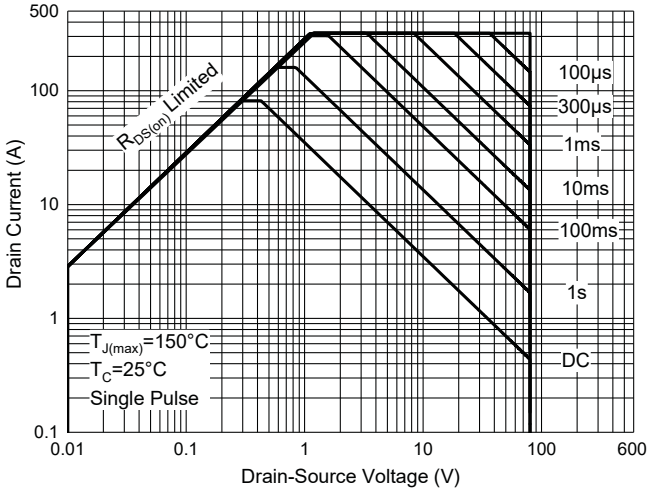


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Safe Operation Area



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel